

Document Title**1M x8 bit Super Low Power and Low Voltage Full CMOS Static RAM****Revision History**

<u>Revision No.</u>	<u>History</u>	<u>Draft Date</u>	<u>Remark</u>
0.0	Initial draft	August 25, 1999	Preliminary
1.0	Finalize - Adopt new code. - Improve V_{IN} , V_{OUT} max. on ABSOLUTE MAXIMUM RATINGS from 3.6V to $V_{CC}+0.3V$.	February 24, 2000	Final
2.0	Revise - Errata correction - Improve V_{IL} max. on RECOMMENDED DC OPERATING CONDITIONS from 0.4V to 0.6V. - Improve V_{IH} min. on RECOMMENDED DC OPERATING CONDITIONS from 2.2V to 2.0V. - Change for tWHZ: 25 to 20ns for 70ns product - Change for tDW: 25 to 30ns for 70ns product	April 26, 2000	Final
2.01	Revise - Errata Correction : Changed 256 x8 columns to 512 x8 columns in the Functional Block Diagram.	January 7, 2002	Final

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1M x 8 bit Super Low Power and Low Voltage Full CMOS Static RAM

FEATURES

- Process Technology: Full CMOS
- Organization: 1M x8
- Power Supply Voltage: 2.3~2.7V
- Low Data Retention Voltage: 1.5V(Min)
- Three state output and TTL Compatible
- Package Type: 48-FBGA-8.00x12.00

GENERAL DESCRIPTION

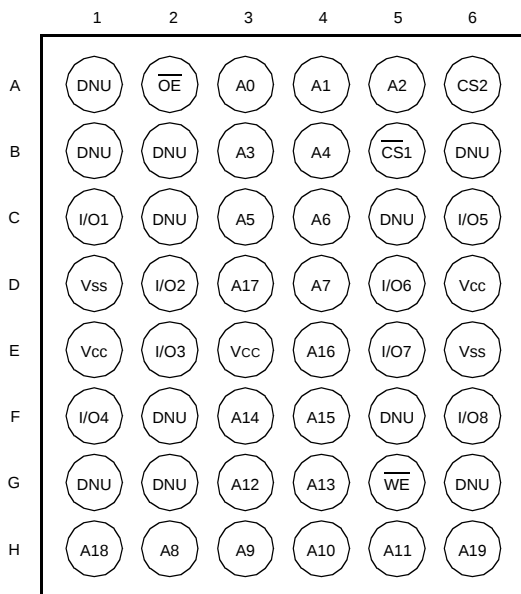
The K6F8008S2M families are fabricated by SAMSUNG's advanced full CMOS process technology. The families support industrial operating temperature ranges and have chip scale package for user flexibility of system design. The families also support low data retention voltage for battery back-up operation with low data retention current.

PRODUCT FAMILY

Product Family	Operating Temperature	Vcc Range	Speed	Power Dissipation		PKG Type
				Standby (Isb1, Typ.)	Operating (Icc1, Max)	
K6F8008S2M-F	Industrial(-40~85°C)	2.3~2.7V	70 ¹ /85ns	0.5μA	2mA	48-FBGA-8.00x12.00

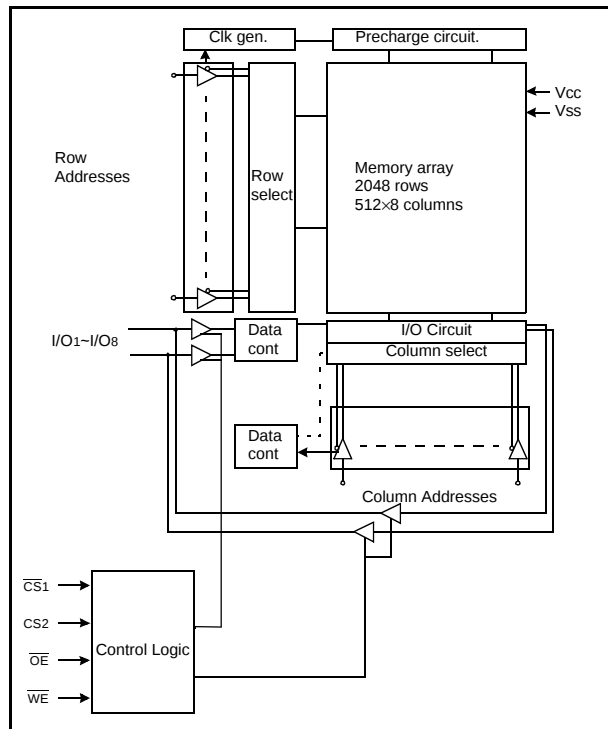
1. The parameter is measured with 30pF test load.

PIN DESCRIPTION



48-FBGA: Top View (Ball Down)

FUNCTIONAL BLOCK DIAGRAM



Name	Function	Name	Function
CS1, CS2	Chip Select Inputs	A0~A19	Address Inputs
OE	Output Enable Input	Vcc	Power
WE	Write Enable Input	Vss	Ground
I/O1~I/O16	Data Inputs/Outputs	DNU	Do Not Use

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PRODUCT LIST

Industrial Temperature Products(-40~85°C)	
Part Name	Function
K6F8008S2M-FF70	48-FBGA, 70ns, 2.5V
K6F8008S2M-FF85	48-FBGA, 85ns, 2.5V

FUNCTIONAL DESCRIPTION

$\overline{CS1}$	CS2	$\overline{OE}$	$\overline{WE}$	I/O1-8	Mode	Power
H	X ¹⁾	X ¹⁾	X ¹⁾	High-Z	Deselected	Standby
X ¹⁾	L	X ¹⁾	X ¹⁾	High-Z	Deselected	Standby
L	H	H	H	High-Z	Output Disabled	Active
L	H	L	H	Dout	Read	Active
L	H	X ¹⁾	L	Din	Write	Active

1. X means don't care. (Must be low or high state)

ABSOLUTE MAXIMUM RATINGS¹⁾

Item	Symbol	Ratings	Unit
Voltage on any pin relative to Vss	V _{IN} , V _{OUT}	-0.2 to V _{CC} +0.3V	V
Voltage on Vcc supply relative to Vss	V _{CC}	-0.2 to 3.6	V
Power Dissipation	P _D	1.0	W
Storage temperature	T _{STG}	-65 to 150	°C
Operating Temperature	T _A	-40 to 85	°C

1. Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation should be restricted to recommended operating condition. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS¹⁾

Item	Symbol	Min	Typ	Max	Unit
Supply voltage	V _{CC}	2.3	2.5	2.7	V
Ground	V _{SS}	0	0	0	V
Input high voltage	V _{IH}	2.0	-	V _{CC} +0.2 ²⁾	V
Input low voltage	V _{IL}	-0.2 ³⁾	-	0.6	V

Note:

1. T_A=-40 to 85°C, otherwise specified2. Overshoot: V_{CC}+1.0V in case of pulse width ≤20ns.

3. Undershoot: -1.0V in case of pulse width ≤20ns.

4. Overshoot and undershoot are sampled, not 100% tested.

CAPACITANCE¹⁾ (f=1MHz, T_A=25°C)

Item	Symbol	Test Condition	Min	Max	Unit
Input capacitance	C _{IN}	V _{IN} =0V	-	8	pF
Input/Output capacitance	C _{IO}	V _{IO} =0V	-	10	pF

1. Capacitance is sampled, not 100% tested

DC AND OPERATING CHARACTERISTICS

Item	Symbol	Test Conditions	Min	Typ	Max	Unit
Input leakage current	I _{LI}	V _{IN} =V _{SS} to V _{CC}	-1	-	1	μA
Output leakage current	I _{LO}	$\overline{CS_1}=V_{IH}$, $\overline{CS_2}=V_{IL}$ or $\overline{OE}=V_{IH}$ or $\overline{WE}=V_{IL}$, V _{IO} =V _{SS} to V _{CC}	-1	-	1	μA
Operating power supply current	I _{CC}	I _{IO} =0mA, $\overline{CS_1}=V_{IL}$, $\overline{CS_2}=V_{IH}$, $\overline{WE}=V_{IH}$, V _{IN} =V _{IH} or V _{IL}	-	-	2	mA
Average operating current	I _{CC1}	Cycle time=1μs, 100%duty, I _{IO} =0mA, $\overline{CS_1} \leq 0.2V$, $\overline{CS_2} \geq V_{CC}-0.2V$, V _{IN} ≤0.2V or V _{IN} ≥V _{CC} -0.2V	-	-	2	mA
	I _{CC2}	Cycle time=Min, I _{IO} =0mA, 100% duty, $\overline{CS_1}=V_{IL}$, $\overline{CS_2}=V_{IH}$, V _{IN} =V _{IL} or V _{IH}	-	-	25	mA
Output low voltage	V _{OL}	I _{OL} = 2.1mA	-	-	0.4	V
Output high voltage	V _{OH}	I _{OH} = -1.0mA	2.0	-	-	V
Standby Current(TTL)	I _{SB}	$\overline{CS_1}=V_{IH}$, $\overline{CS_2}=V_{IL}$, Other inputs=V _{IH} or V _{IL}	-	-	0.3	mA
Standby Current(CMOS)	I _{SB1}	$\overline{CS_1} \geq V_{CC}-0.2V$, $\overline{CS_2} \geq V_{CC}-0.2V$ ($\overline{CS_1}$ controlled) or $\overline{CS_2} \leq 0.2V$ ($\overline{CS_2}$ controlled), Other inputs=0-V _{CC}	-	0.5	20 ¹⁾	μA

1. Super low power product=10μA with special handling.

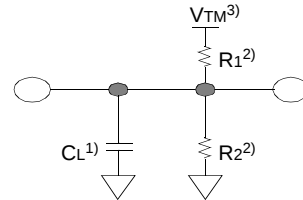
AC OPERATING CONDITIONS

TEST CONDITIONS (Test Load and Input/Output Reference)

Input pulse level: 0.4 to 2.2V

Input rising and falling time: 5ns

Input and output reference voltage: 1.1V

Output load (see right): $C_L=100\text{pF}+1\text{TTL}$ $C_L=30\text{pF}+1\text{TTL}$ 

1. Including scope and jig capacitance

2. $R_1=3070\Omega$, $R_2=3150\Omega$ 3. $V_{TM}=2.3\text{V}$ AC CHARACTERISTICS ($V_{CC}=2.3\sim 2.7\text{V}$, Industrial product: $T_A=-40$ to 85°C)

Parameter List		Symbol	Speed Bins				Units
			70ns		85ns		
			Min	Max	Min	Max	
Read	Read Cycle Time	t _{RC}	70	-	85	-	ns
	Address Access Time	t _{AA}	-	70	-	85	ns
	Chip Select to Output	t _{CO}	-	70	-	85	ns
	Output Enable to Valid Output	t _{OE}	-	35	-	40	ns
	Chip Select to Low-Z Output	t _{LZ}	10	-	10	-	ns
	Output Enable to Low-Z Output	t _{OLZ}	5	-	5	-	ns
	Chip Disable to High-Z Output	t _{HZ}	0	25	0	25	ns
	Output Disable to High-Z Output	t _{OHZ}	0	25	0	25	ns
	Output Hold from Address Change	t _{OH}	10	-	10	-	ns
Write	Write Cycle Time	t _{WC}	70	-	85	-	ns
	Chip Select to End of Write	t _{CW}	60	-	70	-	ns
	Address Set-up Time	t _{AS}	0	-	0	-	ns
	Address Valid to End of Write	t _{AW}	60	-	70	-	ns
	Write Pulse Width	t _{WP}	50	-	60	-	ns
	Write Recovery Time	t _{WR}	0	-	0	-	ns
	Write to Output High-Z	t _{WHZ}	0	20	0	25	ns
	Data to Write Time Overlap	t _{DW}	30	-	35	-	ns
	Data Hold from Write Time	t _{DH}	0	-	0	-	ns
	End Write to Output Low-Z	t _{OW}	5	-	5	-	ns

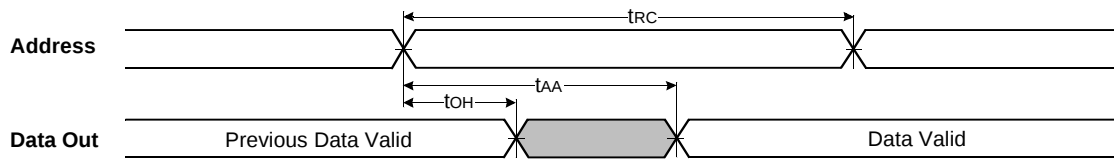
DATA RETENTION CHARACTERISTICS

Item	Symbol	Test Condition	Min	Typ	Max	Unit
V _{CC} for data retention	V _{DR}	$\overline{CS}_1 \geq V_{CC}-0.2\text{V}^{(1)}$	1.5	-	2.7	V
Data retention current	I _{DR}	$V_{CC}=1.5\text{V}$, $\overline{CS}_1 \geq V_{CC}-0.2\text{V}^{(1)}$	-	0.5	6 ⁽²⁾	μA
Data retention set-up time	t _{SDR}	See data retention waveform	0	-	-	ns
Recovery time	t _{RDR}		t _{RC}	-	-	

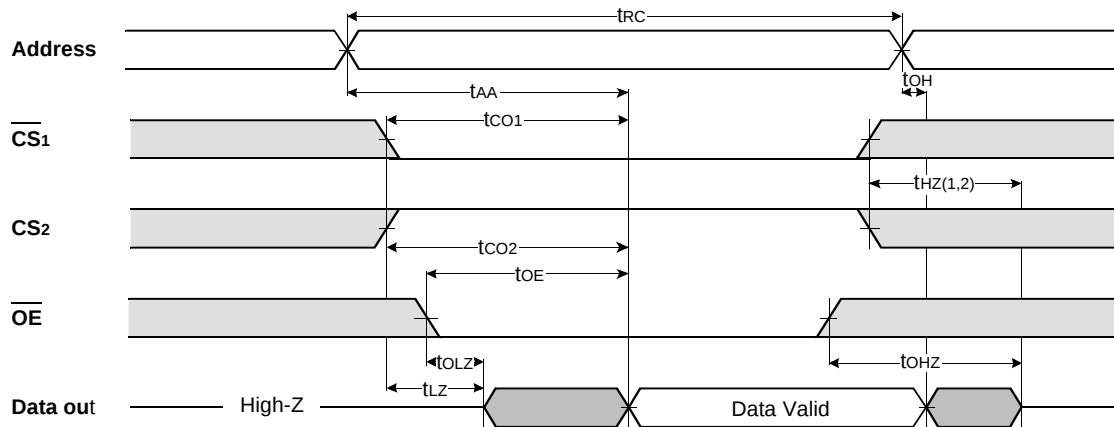
1. $\overline{CS}_1 \geq V_{CC}-0.2\text{V}$, $\overline{CS}_2 \geq V_{CC}-0.2\text{V}$ ($\overline{CS}_1$ controlled) or $\overline{CS}_2 \geq V_{CC}-0.2\text{V}$ ($\overline{CS}_2$ controlled).2. Super low power product=4 μA with special handling.

TIMING DIAGRAMS

TIMING WAVEFORM OF READ CYCLE(1) (Address Controlled, $\overline{CS1}=\overline{OE}=V_{IL}$, $CS2=\overline{WE}=V_{IH}$)



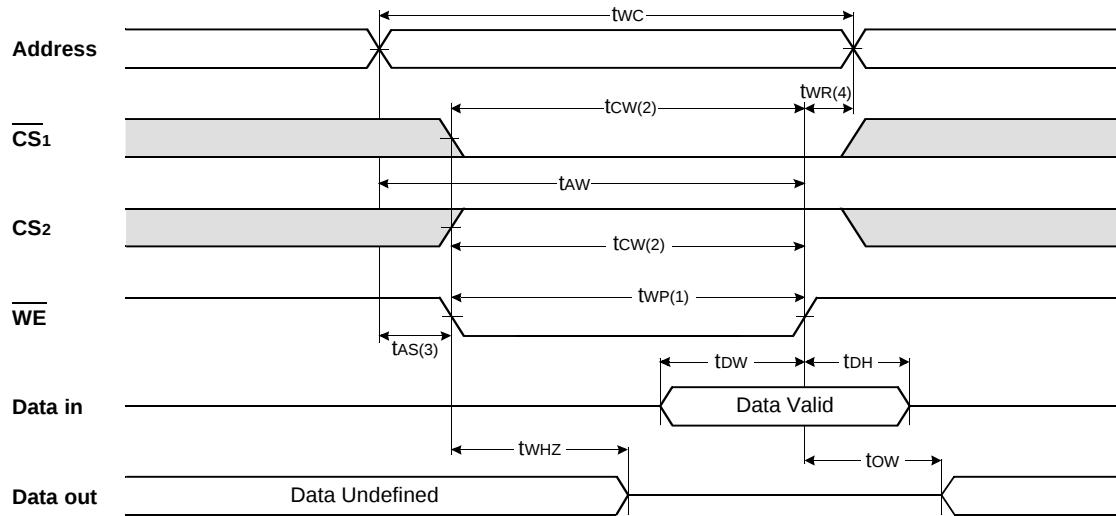
TIMING WAVEFORM OF READ CYCLE(2) ($\overline{WE}=V_{IH}$)



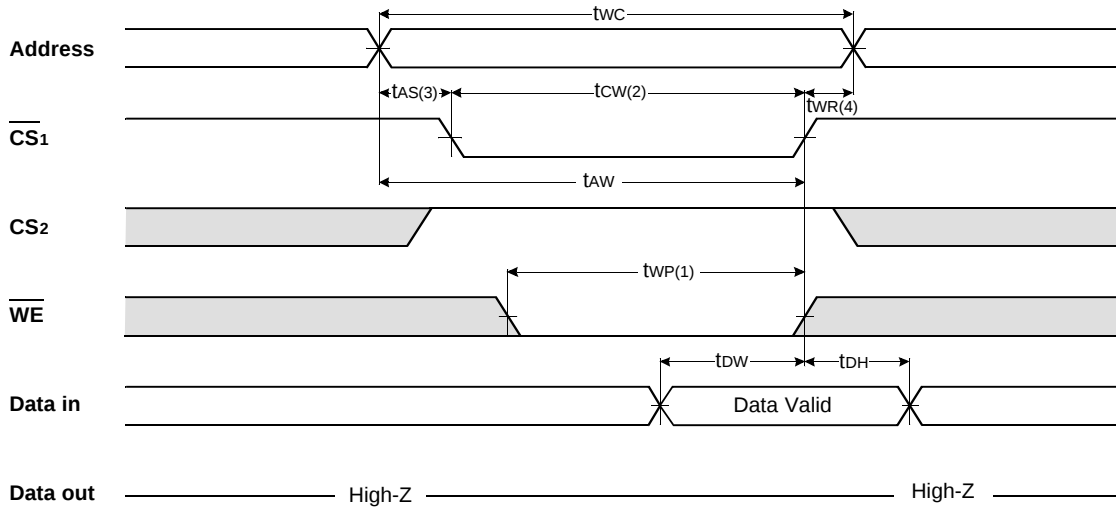
NOTES (READ CYCLE)

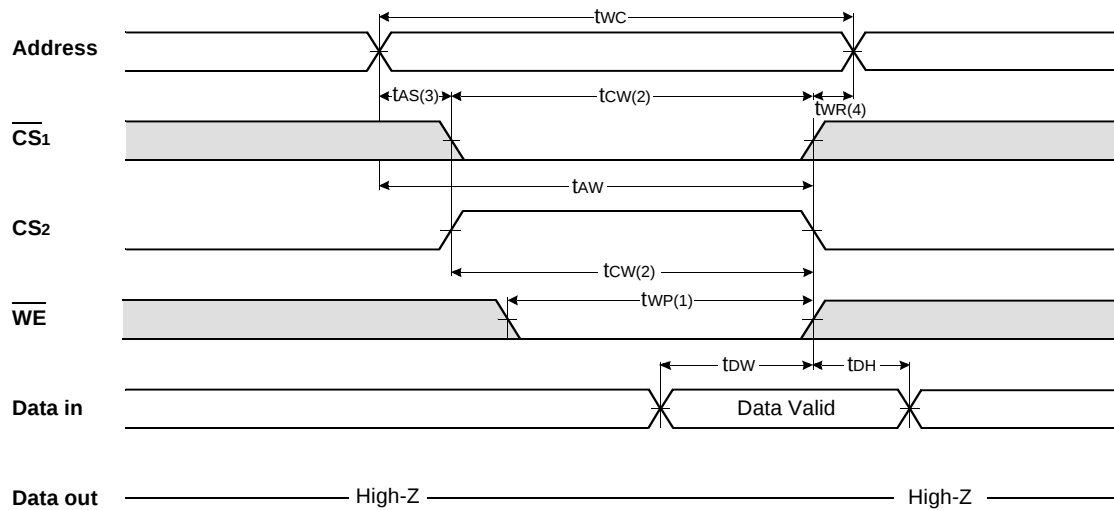
1. t_{HZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.
2. At any given temperature and voltage condition, $t_{HZ}(\text{Max.})$ is less than $t_{LZ}(\text{Min.})$ both for a given device and from device to device interconnection.

TIMING WAVEFORM OF WRITE CYCLE(1) ($\overline{\text{WE}}$ Controlled)



TIMING WAVEFORM OF WRITE CYCLE(2) ($\overline{\text{CS1}}$ Controlled)

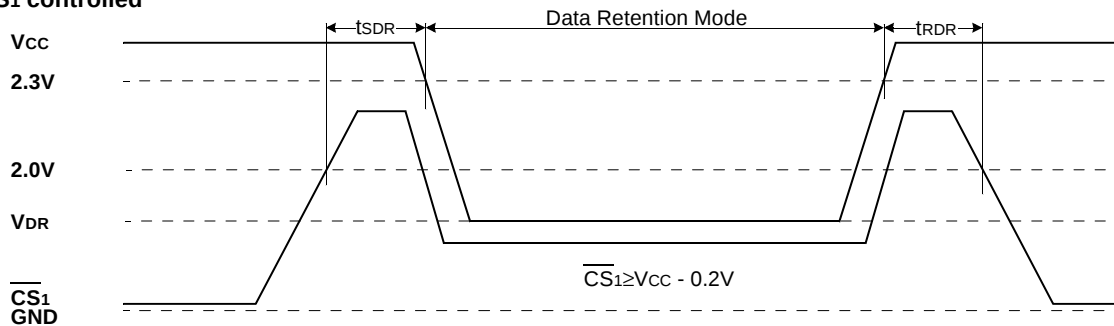
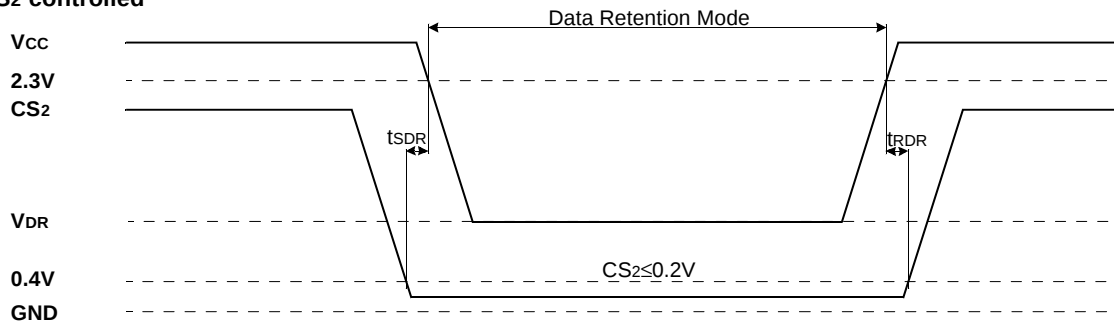


TIMING WAVEFORM OF WRITE CYCLE(3) (CS₂ Controlled)

NOTES (WRITE CYCLE)

1. A write occurs during the overlap of a low $\overline{CS_1}$, a high CS₂ and a low $\overline{WE}$. A write begins at the latest transition among $\overline{CS_1}$ goes low, CS₂ going high and WE going low : A write ends at the earliest transition among CS₁ going high, CS₂ going low and WE going high, tWP is measured from the beginning of write to the end of write.
2. tCW is measured from the CS₁ going low or CS₂ going high to the end of write.
3. tAS is measured from the address valid to the beginning of write.
4. tWR is measured from the end of write to the address change. tWR applied in case a write ends as $\overline{CS_1}$ or $\overline{WE}$ going high tWR2 applied in case a write ends as CS₂ going to low.

DATA RETENTION WAVE FORM

CS₁ controlledCS₂ controlled

PACKAGE DIMENSION

Unit: millimeters

48 BALL FINE PITCH BGA(0.75mm ball pitch)

